

GaAs PIN photodiode with preamp G9287-14

ROSA type, 850 nm, 10 Gbps



Features

- ϕ 1.25 mm sleeve type ROSA (Receiver Optical Sub-Assembly)
- High-speed response: 10 Gbps
- Low power supply voltage: 3.3 V
- Differential output
- Sensitivity: +2 to -14 dBm Typ. (Extinction ratio=4.5 dB)
- Trans-impedance: 6 k Ω Typ. *1

Applications

- 10 gigabit ethernet
- Optical fiber communications

■ Absolute maximum ratings (Ta=25 °C)

Parameter	Symbol	Value	Unit
Supply voltage	Vcc	-0.5, +4	V
Reverse voltage (photodiode)	VR	7	V
Operating temperature	Topr	-20 to +85	°C
Storage temperature	Tstg	-40 to +85	°C

■ Electrical and optical characteristics (Ta=25 °C, 850 nm, Vcc=3.3 \pm 5 % V, Vpd=3.13 to 5.0 V, RL=50 Ω *2, unless otherwise noted)

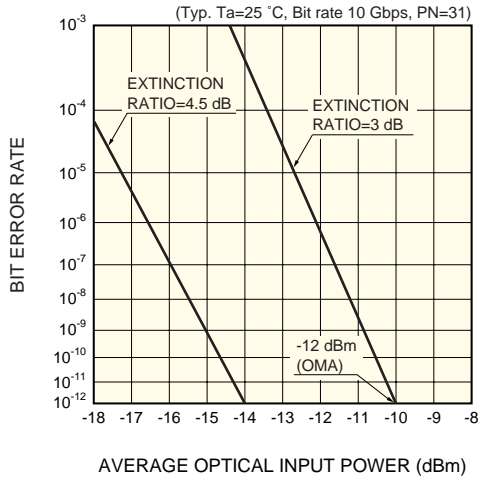
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Responsivity *3	R		0.4	0.55	-	A/W	
Supply current	Icc	Dark state, RL= ∞	-	30	45	mA	
Cut-off frequency	fc	-3 dB	6.5	7.0	-	GHz	
Low cut-off frequency	fc-L	-3 dB	-	20	-	kHz	
Noise equivalent power *1	NEP	Dark state, DC to 7.5 GHz	-	1.5	-	μ W _{rms}	
Trans-impedance *1	Tz	RL=50 Ω , f=100 MHz	4.5	6	-	k Ω	
Minimum receivable sensitivity *3	Pmin	10 Gbps, NRZ, PRBS=2 ³¹ -1, BER=10 ⁻¹²	Extinction ratio=4.5 dB	-	-14	-	dBm
Minimum receivable sensitivity *3 (OMA)	Pmin (OMA)		Extinction ratio=3 dB	-	-10	-	
Maximum receivable sensitivity	Pmax		Extinction ratio=3 dB	-	-12	-	
			Extinction ratio=10 dB	-	+2	-	
Output amplitude	Vomax		350	450	550	mV _{pp}	
Dark current	ID	Dark state, RL= ∞	-	0.05	1	nA	
Optical return loss *3	ORL		12	14	-	dB	

*1: Single-ended (Vout+) measurement

*2: Capacitive coupling

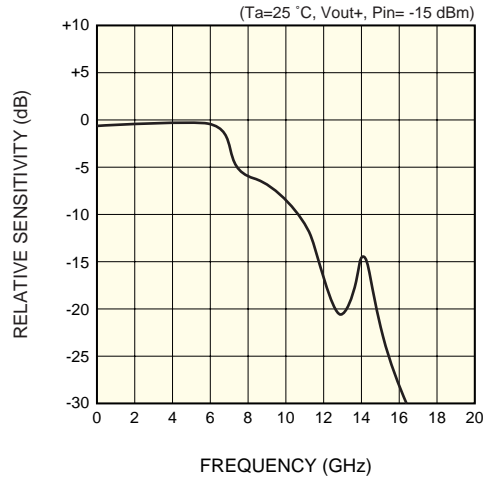
*3: Measurement by 50/125 μ m GI MM fiber

Bit error rate



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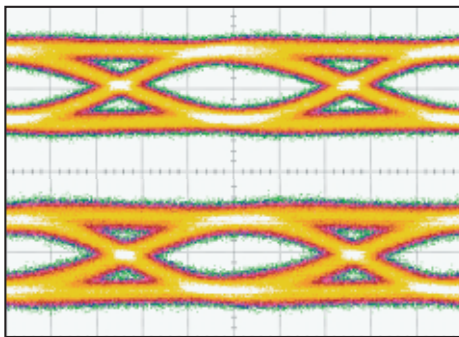
Frequency response



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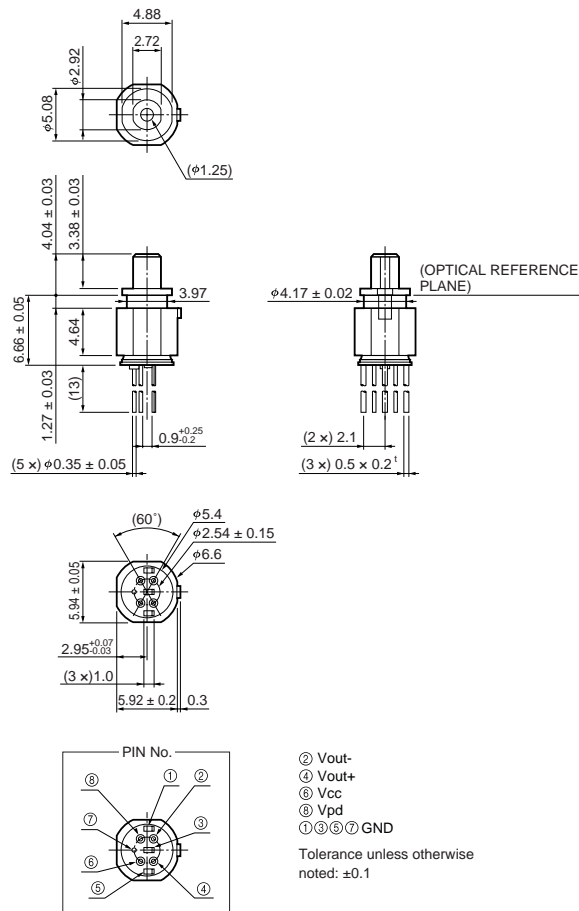
Eye diagram

Bit rate 10 Gbps, PN=31, NRZ, $\lambda=850\text{ nm}$,
Extinction ratio 4.5 dB, $V_{cc}=V_{pd}=3.3\text{ V}$,
Responsivity=0.55 A/W



$P_{in} = -13\text{ dBm}$, 30 mV/div., 20 ps/div.

Dimensional outline (unit: mm)



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